



BY JOHN H. PHELPS

27-mc Silicon Transistorized Superhet Receiver

■ Recently a low cost, high performance series of silicon transistors was announced by General Electric. These transistors are ideally suited to 27-mc R/C superhet service and offer outstanding performance in this application. The principal advantage to the user provided by a silicon transistor is very low leakage current. This, in turn, allows circuit simplification and far better high temperature performance. The uniformly high current gain inherent in these units provides excellent sensitivity with generous margin against receiver sensitivity decrease as temperature drops to winter flying levels.

Circuit Description: Q_2 , the mixer rt. pg. selects the proper channel as determined by the crystal X in the oscillator Q_1 and converts the signal to an intermediate frequency of 456-kc. The antenna, shown connected to the top end of

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